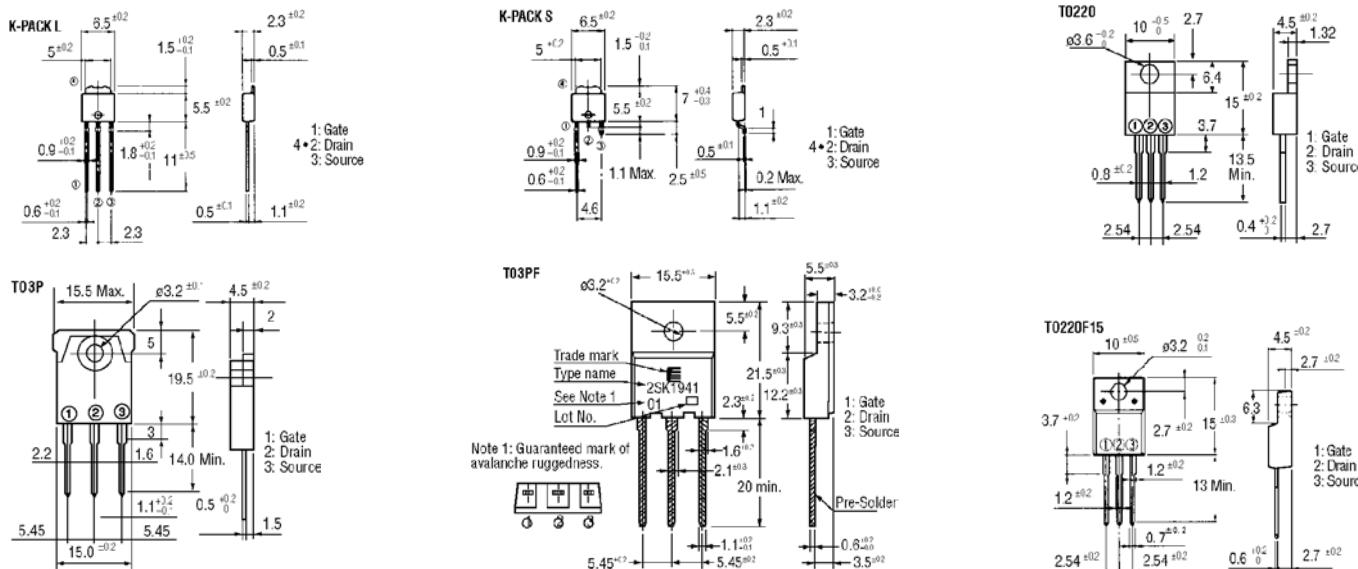


## N-Channel Silicon Power MOS-FET



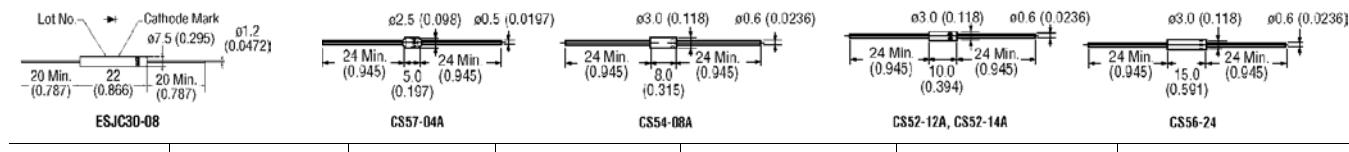
► F-I Series = Low RDS(ON)  
 ► F-II Series = VGS  $\pm 30$  V, Reduced Turn Off Time  
 ► F-III Series = Logic Level, High g<sub>s</sub>  
 ► FAP-II Series = High Avalanche Ruggedness

► F-III Series = Logic Level, High g<sub>s</sub>  
 ► FAP-III = Logic Level, High Avalanche Ruggedness  
 ► FAP-II = VGS  $\pm 35$  V, VGS(th) 4.0  $\pm 0.5$  V

► FAP-IIA = Reduced Turn Off Time  
 ► FAP-IIIIB = High Speed Non Logic  
 ► FAP-IIIB = Logic Level, VGS(th) 1.5  $\pm 0.5$  V

Mfr.'s type	Series	Ratings			Characteristics					Package	
		V <sub>oss</sub> (V)	I <sub>b</sub> (A)	P <sub>d</sub> (W)	R <sub>DSON</sub> (ON) (Ω) (Max.)		C <sub>iss</sub> (pF)	C <sub>oss</sub> (pF)	t <sub>on</sub> (ns)	t <sub>off</sub> (ns)	
					V <sub>GS</sub> =4V	V <sub>GS</sub> =10V					
2SJ314-01L	FAP-III	-60	-5.0	20	0.480	0.300	750	300	53	270	K-PACK L
2SJ314-01S	FAP-III	-60	-5.0	20	0.480	0.300	750	300	53	270	K-PACK S
2SK2248-01L	FAP-III	30	35.0	60	0.037	0.022	2630	1200	188	720	K-PACK L
2SK2248-01S	FAP-III	30	35.0	60	0.037	0.022	2630	1200	188	720	K-PACK S
2SK2687-01	FAP-III	30	50.0	60	0.017	0.010	4130	1950	103	520	TO220
2SK2693-01	FAP-IIIIB	30	100.0	150	0.007	0.004	9900	4950	260	1270	TO3P
2SK2900-01	FAP-IIIIB	60	45.0	60	—	0.140	3450	1370	110	200	TO220
2SK2690-01	FAP-III	60	80.0	125	0.017	0.010	5250	1870	143	450	TO3P
2SK2906-01	FAP-IIIIB	60	100.0	150	—	0.007	8100	3150	400	470	TO3P
2SK3270-01	Trench	60	80.0	135	—	0.006	9000	1250	250	285	TO-220
2SK3271-01	Trench	60	100.0	155	—	0.006	9000	1250	250	285	TO3P
2SK3216-01	FAP-IIIIBH	100	45.0	80	—	0.026	4800	1140	186	240	TO220
2SK3217-01MR	FAP-IIIIBH	100	50.0	70	—	0.025	4800	1140	230	265	TO-220F15
2SK3218-01	FAP-IIIIBH	150	35.0	80	—	0.048	3900	800	158	270	TO220
2SK3219-01MR	FAP-IIIIBH	150	40.0	70	—	0.043	3980	830	174	263	TO-220F15
2SK2521-01	FAP-III	200	18.0	50	—	0.180	1650	330	150	150	TO220
2SK3262-01MR	FAP-IIIIB	200	20.0	45	0.15	0.100	2550	435	85	520	TO-220F15
2SK900	F-I	250	12.0	80	—	0.300	1800	300	75	260	TO3P
2SK902	F-I	250	30.0	150	—	0.100	3900	900	200	1000	TO3P
2SK1017-01	F-II	450	20.0	150	—	0.350	3300	480	375	740	TO3P
2SK2021-01	FAP-IIIA	500	5.0	60	—	1.600	1500	130	55	100	TO220
2SK2642-01MR	FAP-IIIS	500	15.0	50	—	0.550	2100	380	220	230	TO220F15
2SK2757-01	FAP-IIIIS	500	10.0	80	—	0.900	950	180	25	60	TO220
2SK725	F-I	500	15.0	125	—	0.380	4000	500	130	440	TO3P
2SK1941-01R	FAP-IIIA	600	16.0	100	—	0.550	4950	470	165	420	TO220
2SK2646-01	FAP-II	800	4.0	80	—	4.000	450	75	20	50	TO220
2SK956-01	FAP-II	800	9.0	150	—	1.500	2100	300	425	690	TO3P
2SK2648-01	FAP-IIIS	800	9.0	150	—	1.500	1200	180	30	95	TO3P
2SK2654-01	FAP-IIIS	900	8.0	150	—	2.000	1200	180	30	95	TO3P
2SK2082-01	FAP-IIIA	900	9.0	150	—	1.400	3300	320	130	320	TO3P
2SK1986-01	FAP-II	1000	4.0	80	—	3.600	1950	150	55	160	TO220
2SK2258-01	FAP-II	1000	4.0	100	—	3.600	1950	150	55	160	TO3P

## Fast Recovery High Voltage Silicon Rectifiers



Notes: \*Single phase; half sine wave in oil bath or filled epoxy at ambient temperature 25°C. \*\*1/2 cycle, 60 Hz at full load. †Reverse Recovery Time: "A" Type — 80 nsec max. @ T<sub>a</sub> = 25°C, I<sub>r</sub> = 2 mA, I<sub>R</sub> = 1 mA; Non "A" Type — 100 nsec max. @ T<sub>a</sub> = 25°C, I<sub>r</sub> = 2 mA, I<sub>R</sub> = 1 mA. Storage and Operating Junction Temperature, T<sub>j</sub>: -65°C to +150°C. Packaging: Bulk or tape and reel available (please specify).

Same Day Shipments For Product In Stock

ALLIED ▶ 803